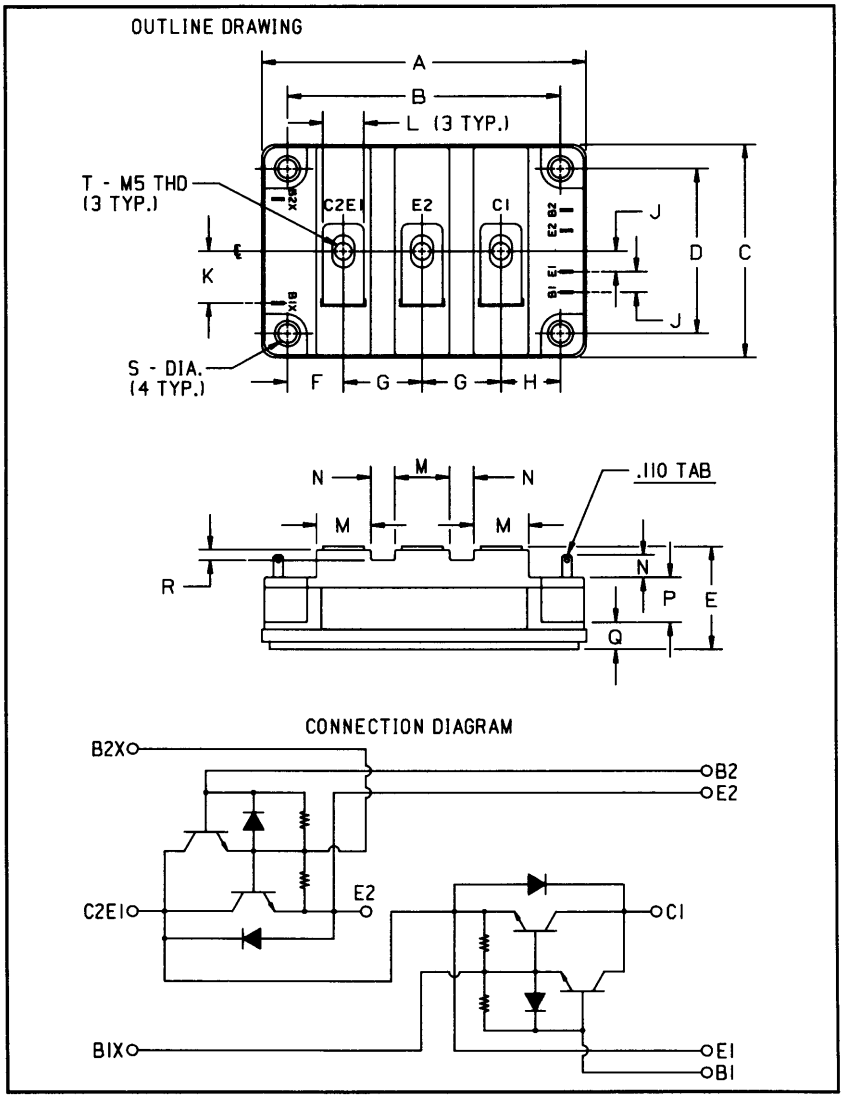
Powerex, Inc., 200 Hillis Street, Youngwood, Pennsylvania 15697-1800 (412) 925-7272

Dual Darlington Transistor Module

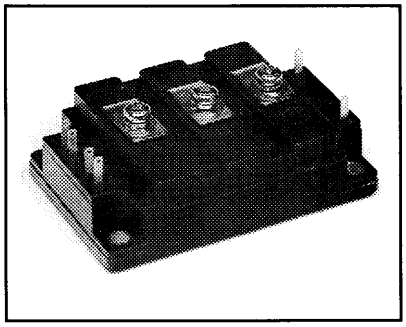
100 Amperes/600 Volts



Outline Drawing

Dimensions	Inches	Millimeters
A	3.740 Max.	95 Max.
B	3.150 ± 0.01	80 ± 0.25
C	2.441 Max.	62 Max.
D	1.890 ± 0.01	48 ± 0.25
E	1.181 Max.	30 Max.
F	0.650	16.5
G	0.906	23
H	0.689	17.5
J	0.236	6

Dimensions	Inches	Millimeters
K	0.596	15
L	0.472	12
M	0.630	16
N	0.276	7
P	0.512	13
Q	0.315	8
R	0.118	3
S	0.216 Dia.	5.5 Dia.
T	M5 Metric	M5



Description:
The Powerex Dual Darlington Transistor Modules are high power devices designed for use in switching applications. The modules are isolated, consisting of two Darlington Transistors with each transistor having a reverse parallel connected high-speed diode.

Features:
- ☐ Isolated Mounting
- ☐ Planar Chips
- ☐ Discrete Fast Recovery Feedback Diode
- ☐ High Gain (h_{FE})
- ☐ Quick Connect Base-Emitter Signal Terminals
- ☐ Base-Emitter Speed-up Diodes

Applications:
- ☐ AC Motor Control
- ☐ DC Motor Control
- ☐ Switching Power Supplies
- ☐ Inverters

Ordering Information:
Example: Select the complete eight digit module part number you desire from the table - i.e. KD324510 is a 450 $V_{CEO(sus)}$ (600 V_{CEV}), 100 Ampere Dual Darlington Module.

Type	$V_{CEO(sus)}$ Volts (X 10)	Current Rating Amperes (X 10)
KD32	45	10

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KD324510
Dual Darlington Transistor Module
100 Amperes/600 Volts

Absolute Maximum Ratings, T_j = 25 °C unless otherwise specified

Ratings	Symbol	KD324510	Units
Junction Temperature	T_j	-40 to 150	°C
Storage Temperature	T_{stg}	-40 to 125	°C
Collector-Emitter Sustaining Voltage	$V_{CEO(sus)}$	450	Volts
Collector-Emitter Sustaining Voltage, V_{BE} = -2V	$V_{CEV(sus)}$	600	Volts
Collector-Base Voltage	V_{CBO}	600	Volts
Emitter-Base Voltage	V_{EBO}	7	Volts
Collector-Emitter Voltage, V_{BE} = -2V	V_{CEV}	600	Volts
Continuous Collector Current	I_C	100	Amperes
Diode Forward Current	I_{FM}	100	Amperes
Continuous Base Current	I_B	6	Amperes
Diode Surge Current	I_{FSM}	1000	Amperes
Power Dissipation (Each Transistor)	P_t	620	Watts
Max. Mounting Torque M5 Terminal Screws	–	17	in.-lb.
Max. Mounting Torque M5 Mounting Screws	–	17	in.-lb.
Module Weight (Typical)	–	420	Grams
V Isolation	V_{RMS}	2500	Volts

Electrical Characteristics, T_j = 25 °C unless otherwise specified

Characteristics		Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector Cutoff Current		I_{CEV}	V_{CE} = 600V, V_{BE} = -2V	–	–	2	mA
			V_{CE} = 600V, V_{BE} = -2V, T_C = 125°C	–	–	15	mA
Emitter Cutoff Current		I_{EBO}	V_{EB} = 7V	–	–	100	mA
DC Current Gain		h_{FE}	I_C = 100A, V_{CE} = 2V	75	–	–	–
			I_C = 100A, V_{CE} = 5V	100	–	–	–
Diode Forward Voltage		V_{FM}	I_{FM} = 100A	–	–	1.75	Volts
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	I_C = 100A, I_B = 1.3A	–	–	2.0	Volts
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	I_C = 100A, I_B = 1.3A	–	–	2.5	Volts
Resistive	Turn-on	t_{on}	V_{CC} = 300V	–	–	2.0	µs
Load	Storage Time	t_s	I_C = 100A	–	–	12	µs
Switch Times	Fall Time	t_f	I_{B1} = 2A, I_{B2} = -2A	–	–	3.0	µs

Thermal and Mechanical Characteristics, T_j = 25 °C unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Case-to-Sink	$R_{\theta(c-s)}$	Per 1/2 Module	–	–	0.1	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta(j-c)}$	Transistor Part	–	–	0.2	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta(j-c)}$	Diode Part	–	–	0.65	°C/W